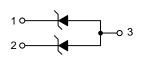
### These dual monolithic silicon surge protection diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.



PIN 1. CATHODE 2. CATHODE 3. ANODE

## Specification Features:

THINK CHANGE DC

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range 5.0 V to 36 V
- Peak Power 300 Watt (8/20 μs)
- Low Leakage 1.0 μA
- Flammability Rating UL 94 V-0
- These are Pb–Free Devices

### **Mechanical Characteristics:**

CASE: Void-Free, Transfer-Molded, Thermosetting Plastic Case FINISH: Corrosion Resistant Finish, Easily Solderable MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds

Package Designed for Optimal Automated Board Assembly

Small Package Size for High Density Applications

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 20 $\mu s$ (Note 1) @ $T_L \leq 25^\circ C$	P <sub>pk</sub>	300	W
IEC 61000–4–2 (ESD) Air Contact		±15 ±26	kV
IEC 61000-4-4 (EFT)		40	A
IEC 61000–4–5 (Lightning)		12	A
Total Power Dissipation on FR–5 Board (Note 2) @ T <sub>A</sub> = 25°C Derate above 25°C Thermal Resistance, Junction–to–Ambient	Ρ <sub>D</sub> R <sub>θJA</sub>	225 1.8 556	mW mW/°C °C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ T <sub>A</sub> = 25°C Derate above 25°C Thermal Resistance, Junction–to–Ambient	P <sub>D</sub> R <sub>θJA</sub>	300 2.4 417	mW mW/°C °C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	٥C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 3

2. FR-5 = 1.0 x 0.75 x 0.62 in.

3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

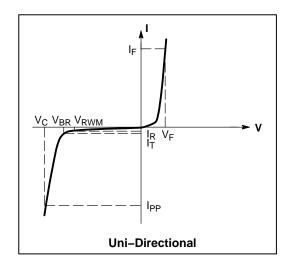
NOTE: Other voltages may be available upon request

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**ELECTRICAL CHARACTERISTICS** 

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

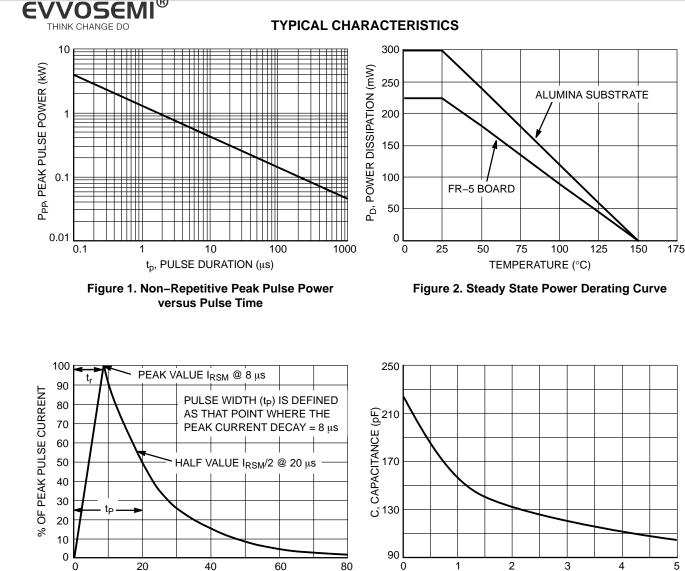
Symbol	Parameter				
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current				
V <sub>C</sub>	Clamping Voltage @ IPP				
V <sub>RWM</sub>	Working Peak Reverse Voltage				
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>				
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>				
Ι <sub>Τ</sub>	Test Current				
$\Theta V_{BR}$	Maximum Temperature Coefficient of $V_{BR}$				
١ <sub>F</sub>	Forward Current				
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>				
Z <sub>ZT</sub>	Maximum Zener Impedance @ I <sub>ZT</sub>				
I <sub>ZK</sub>	Reverse Current				
Z <sub>ZK</sub>	Maximum Zener Impedance @ I <sub>ZK</sub>				



# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

				V <sub>BR</sub> , Breakd	own Voltage		V <sub>C</sub> @ I <sub>PP</sub> =	Max I <sub>PP</sub>	Typical Capacitance
		V <sub>RWM</sub>	I <sub>R</sub> @ V <sub>RWM</sub>	(Vo	lts)	Ι <sub>Τ</sub>	1 Amp	(Note 4)	(pF)
Device*	Device Marking	(Volts)	(μA)	Min	Max	mA	(Volts)	(Amps)	Pin 1 to 3 @ 0 Volts
SM05T1G	05M	5	10	6.2	7.3	1.0	9.8	17	225
SM12T1G	12M	12	1.0	13.3	15.75	1.0	19	12	95
SM15T1G	15M	15	1.0	16.7	19.6	1.0	24	10	100
SM24T1G	24M	24	1.0	26.7	31.35	1.0	43	5.0	60
SM36T1G	36M	36	1.0	40.0	46.95	1.0	60	4.0	45

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4.  $8/20 \ \mu s$  pulse waveform per Figure 3



t, TIME (µs) Figure 3. 8/20 µs Pulse Waveform

**BIAS VOLTAGE (VOLTS)** Figure 4. Typical Diode Capacitance (SM05)

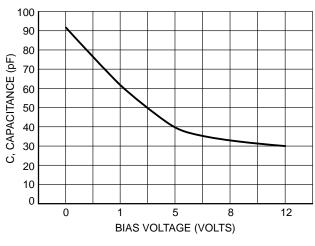


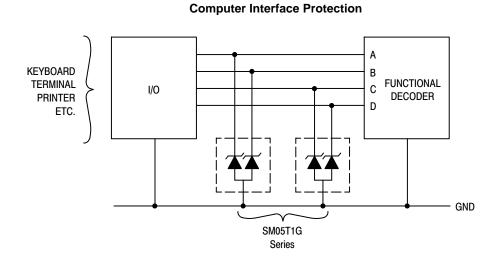
Figure 5. Typical Diode Capacitance (SM12)



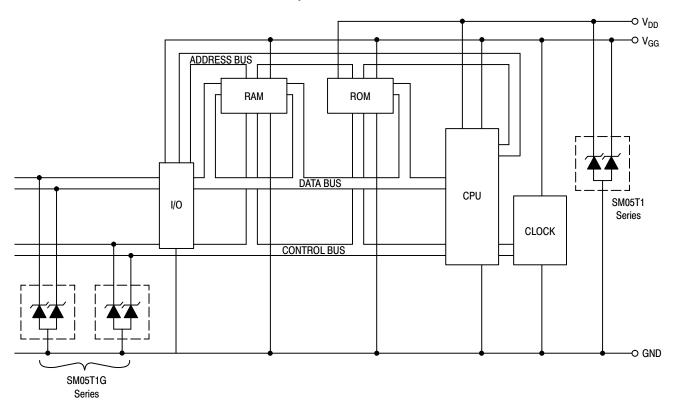
## **TYPICAL COMMON ANODE APPLICATIONS**

A quad junction common anode design in a SOT-23 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of surge protection applications are illustrated below.



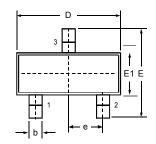
**Microprocessor Protection** 

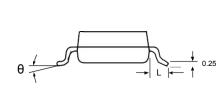




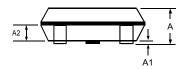
SMxxT1G

# Outline Drawing - SOT-23

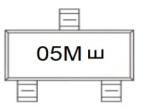




DIMENSIONS					
SYMBOL	MILLIN	<b>IETER</b>	INCHES		
OTHEOL	MIN	MAX	MIN	MAX	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
D	2.800	3.000	0.110	0.118	
b	0.300	0.500	0.012	0.020	
E	2.250	2.550	0.089	0.100	
E1	1.200	1.400	0.047	0.055	
е	0.950 BSC		0.037	BSC	
L	0.500	0.675	0.020	0.027	
θ	0	<b>8</b> °	0	<b>8</b> °	



Marking



# **Ordering information**

Order code	Package	Baseqty	Delivery mode
SM05T1G	SOT-23	3000	Tape and reel
SM12T1G	SOT-23	3000	Tape and reel
SM15T1G	SOT-23	3000	Tape and reel
SM24T1G	SOT-23	3000	Tape and reel
SM36T1G	SOT-23	3000	Tape and reel